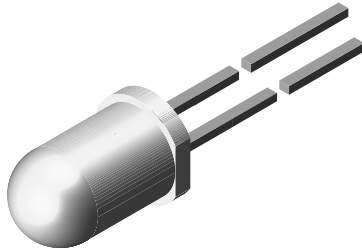


Infrared Emitting Diode, 875 nm, GaAlAs



94 8389

FEATURES

- Package type: leaded
- Package form: T-1 $\frac{3}{4}$
- Dimensions (in mm): \varnothing 5
- Peak wavelength: $\lambda_p = 875$ nm
- High reliability
- Angle of half intensity: $\varphi = \pm 12^\circ$
- Low forward voltage
- Suitable for high pulse current operation
- Good spectral matching with Si photodetectors
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition



RoHS
COMPLIANT
HALOGEN
FREE

DESCRIPTION

The TSHA620. series are infrared, 875 nm emitting diodes in GaAlAs technology, molded in a clear, untinted plastic package.

APPLICATIONS

- Infrared remote control and free air data transmission systems
- This emitter series is dedicated to systems with panes in transmission space between emitter and detector, because of the low absorption of 875 nm radiation in glass

PRODUCT SUMMARY

COMPONENT	I_e (mW/sr)	φ (deg)	λ_p (nm)	t_r (ns)
TSHA6200	40	± 12	875	600
TSHA6201	50	± 12	875	600
TSHA6202	60	± 12	875	600
TSHA6203	65	± 12	875	600

Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
TSHA6200	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1 $\frac{3}{4}$
TSHA6201	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1 $\frac{3}{4}$
TSHA6202	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1 $\frac{3}{4}$
TSHA6203	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1 $\frac{3}{4}$

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V_R	5	V
Forward current		I_F	100	mA
Peak forward current	$t_p/T = 0.5, t_p = 100 \mu s$	I_{FM}	200	mA
Surge forward current	$t_p = 100 \mu s$	I_{FSM}	2.5	A
Power dissipation		P_V	180	mW
Junction temperature		T_j	100	$^\circ C$
Operating temperature range		T_{amb}	- 40 to + 85	$^\circ C$
Storage temperature range		T_{stg}	- 40 to + 100	$^\circ C$
Soldering temperature	$t \leq 5$ s, 2 mm from case	T_{sd}	260	$^\circ C$
Thermal resistance junction/ambient	J-STD-051, leads 7 mm, soldered on PCB	R_{thJA}	230	K/W

Note

$T_{amb} = 25 \text{ }^\circ C$, unless otherwise specified

TSHA6200, TSHA6201, TSHA6202, TSHA6203

Vishay Semiconductors Infrared Emitting Diode, 875 nm, GaAlAs

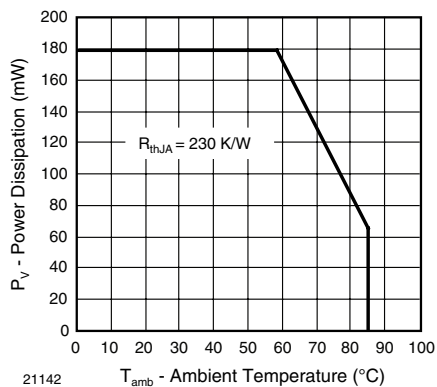


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

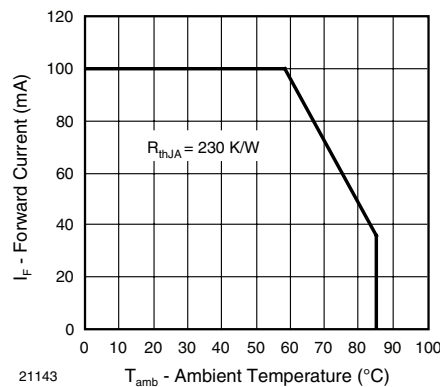


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	I _F = 100 mA, t _p = 20 ms	V _F		1.5	1.8	V
Temperature coefficient of V _F	I _F = 100 mA	TK _{V_F}		- 1.6		mV/K
Reverse current	V _R = 5 V	I _R			100	μA
Junction capacitance	V _R = 0 V, f = 1 MHz, E = 0	C _j		20		pF
Temperature coefficient of φ _e	I _F = 20 mA	TKφ _e		- 0.7		%/K
Angle of half intensity		φ		± 12		deg
Peak wavelength	I _F = 100 mA	λ _p		875		nm
Spectral bandwidth	I _F = 100 mA	Δλ		80		nm
Temperature coefficient of λ _p	I _F = 100 mA	TKλ _p		0.2		nm/K
Rise time	I _F = 100 mA	t _r		600		ns
	I _F = 1 A	t _r		300		ns
Fall time	I _F = 100 mA	t _f		600		ns
	I _F = 1 A	t _f		300		ns
Virtual source diameter		d		3.7		mm

Note

T_{amb} = 25 °C, unless otherwise specified



TSHA6200, TSHA6201, TSHA6202, TSHA6203

Infrared Emitting Diode, 875 nm, GaAlAs Vishay Semiconductors

TYPE DEDICATED CHARACTERISTICS							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 1 \text{ A}$, $t_p = 100 \mu\text{s}$	TSHA6200	V_F		2.8	3.5	V
		TSHA6201	V_F		2.8	3.5	V
		TSHA6202	V_F		2.8	3.5	V
		TSHA6203	V_F		2.8	3.5	V
Radiant intensity	$I_F = 100 \text{ mA}$, $t_p = 20 \text{ ms}$	TSHA6200	I_e	25	40	125	mW/sr
		TSHA6201	I_e	30	50	125	mW/sr
		TSHA6202	I_e	36	60	125	mW/sr
		TSHA6203	I_e	50	65	125	mW/sr
	$I_F = 1 \text{ A}$, $t_p = 100 \mu\text{s}$	TSHA6200	I_e	200	330		mW/sr
		TSHA6201	I_e	260	400		mW/sr
		TSHA6202	I_e	330	460		mW/sr
		TSHA6203	I_e	400	530		mW/sr
Radiant power	$I_F = 100 \text{ mA}$, $t_p = 20 \text{ ms}$	TSHA6200	ϕ_e		22		mW
		TSHA6201	ϕ_e		23		mW
		TSHA6202	ϕ_e		24		mW
		TSHA6203	ϕ_e		25		mW

Note

$T_{amb} = 25 \text{ }^\circ\text{C}$, unless otherwise specified

BASIC CHARACTERISTICS

$T_{amb} = 25 \text{ }^\circ\text{C}$, unless otherwise specified

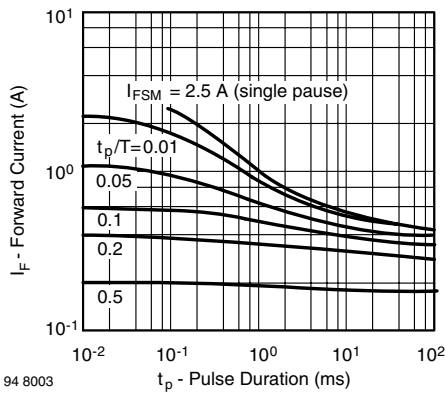


Fig. 3 - Pulse Forward Current vs. Pulse Duration

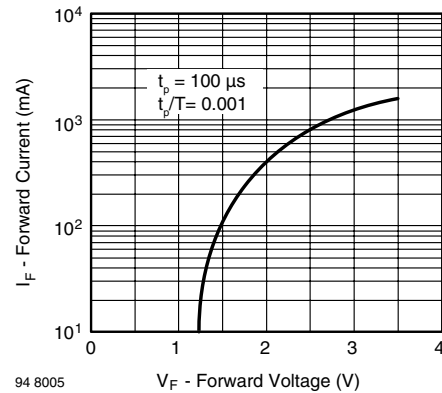


Fig. 4 - Forward Current vs. Forward Voltage

TSHA6200, TSHA6201, TSHA6202, TSHA6203



Vishay Semiconductors Infrared Emitting Diode, 875 nm, GaAlAs

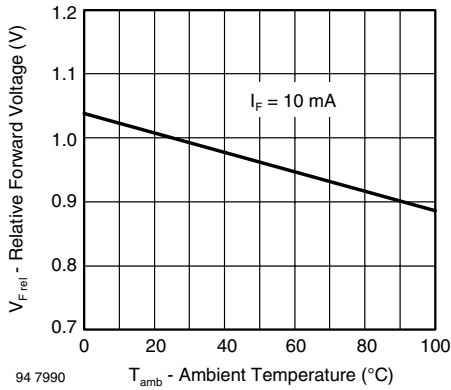


Fig. 5 - Relative Forward Voltage vs. Ambient Temperature

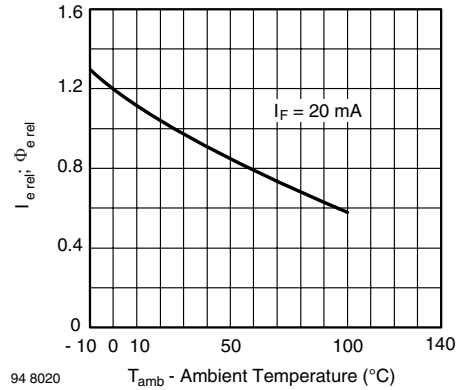


Fig. 8 - Relative Radiant Intensity/Power vs. Ambient Temperature

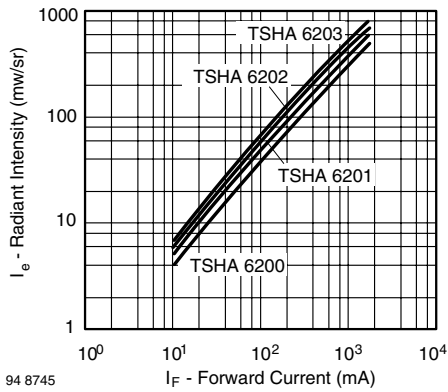


Fig. 6 - Radiant Intensity vs. Forward Current

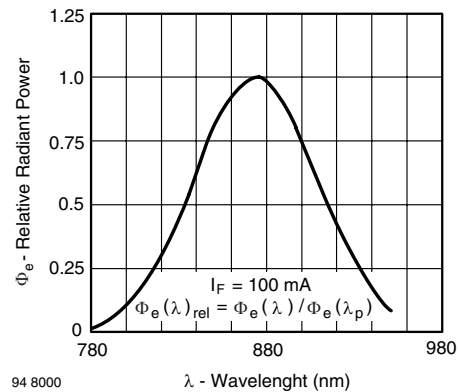


Fig. 9 - Relative Radiant Power vs. Wavelength

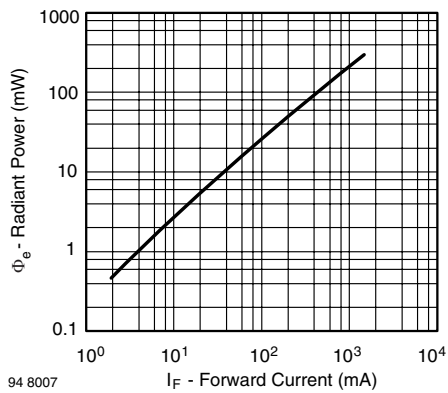


Fig. 7 - Radiant Power vs. Forward Current

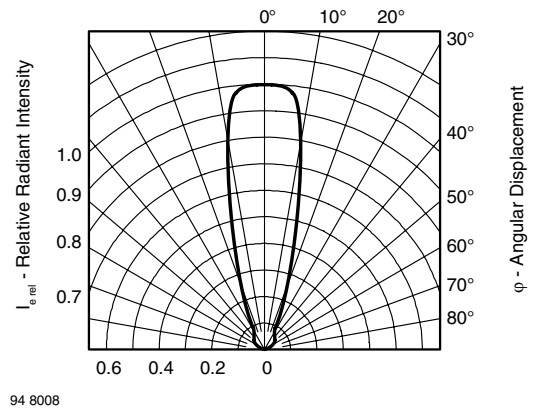


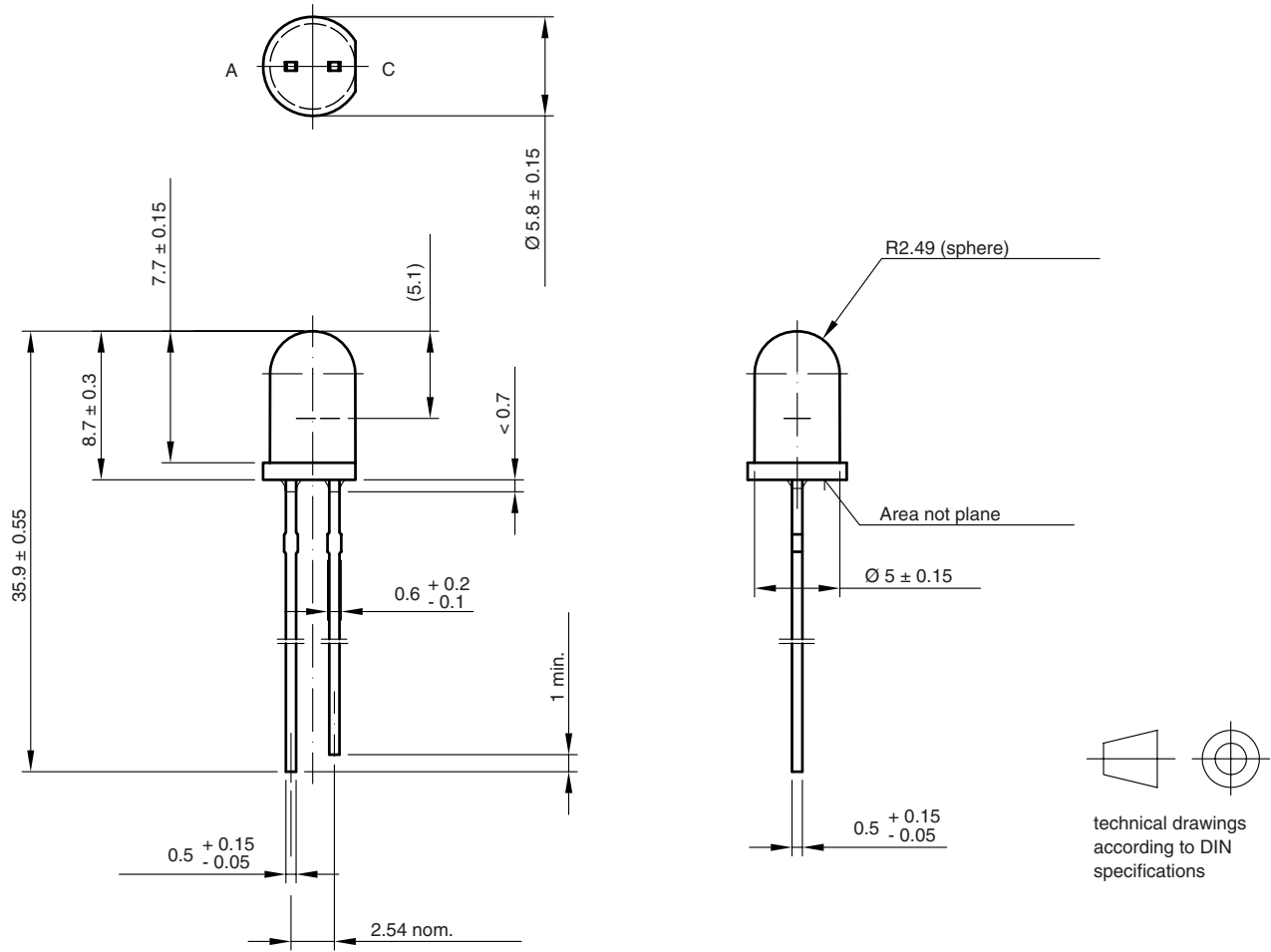
Fig. 10 - Relative Radiant Intensity vs. Angular Displacement



TSHA6200, TSHA6201, TSHA6202, TSHA6203

Infrared Emitting Diode, 875 nm, GaAlAs Vishay Semiconductors

PACKAGE DIMENSIONS in millimeters



Drawing-No.: 6.544-5259.04-4
Issue: 8; 19.05.09
96 12125



Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk and agree to fully indemnify and hold Vishay and its distributors harmless from and against any and all claims, liabilities, expenses and damages arising or resulting in connection with such use or sale, including attorneys fees, even if such claim alleges that Vishay or its distributor was negligent regarding the design or manufacture of the part. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.